DUSEU

NL27WZU04

• Source/Sink 24 mA at 3.0 V

• Chip Complexity < 100 FETs

Qualified and PPAP Capable

A1

A2

1

1

Compliant

Features

operating from a 1.65 to 5.5 V supply.

• Input Overvoltage Tolerant up to 5.5 V

• Source/Sink 12 mA at 3.0 V (NLV)

Dual Unbuffered Inverter MARKING DIAGRAMS 6 Π SC-88 XXXM = DF SUFFIX The NL27WZU04 is a high performance dual unbuffered inverter CASE 419B . • Designed for 1.65 V to 5.5 V V_{CC} Operation SC-74 CASE318F-05 • IOFF Supports Partial Power Down Protection TSOP-6 • Available in SC-88, SC-74, TSOP-6 and UDFN6 Packages XXX M= CASE 318G-02 0 . • NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 UDFN6 1.45 x 1.0 ΧМ • These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS CASE 517AQ UDFN6 1.0 x 1.0 ХМ Y1 CASE 517BX Y2 X, XXX = Specific Device Code = Date Code* М Figure 1. Logic Symbol =Assembly Location

А Y

W

= Year = Work Week

= Pb-Free Package (Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

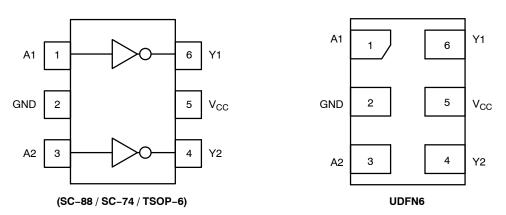
ORDERING INFORMATION See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.

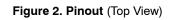
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П





PIN ASSIGNMENT

Pin	Function
1	A1
2	GND
3	A2
4	Y2
5	V _{CC}
6	Y1

FUNCTION TABLE

A Input	Y Output
L	Н
Н	L

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V _{CC}	DC Supply Voltage	SC-88 (NLV), TSOP-6 SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{IN}	DC Input Voltage	SC-88 (NLV), TSOP-6 SC-88, SC-74, UDFN6	−0.5 to +7.0 −0.5 to +6.5	V
V _{OUT}	DC Output Voltage		–0.5 to V _{CC} + 0.5	V
Ι _{ΙΚ}	DC Input Diode Current	V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current	±50	mA	
I _{OUT}	DC Output Source/Sink Current	±50	mA	
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
PD	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 300 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model (NLV) Charged Device Model	2000 1000 N/A	V
I _{Latchup}	Latchup Performance (Note 4)	(NLV)	±500 ±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Applicable to devices with outputs that may be tri-stated.
Applicable to devices with outputs that may be tri-stated.
Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage	0	V _{CC}	
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{cc}	T _A = 25°C			–55°C ≤ T _A ≤ 125°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
VIH	High-Level Input		1.65 to 1.95	0.85 V _{CC}	-	-	0.85 V _{CC}	-	V
	Voltage		2.3 to 5.5	0.80 V _{CC}	-	-	0.80 V _{CC}	_	
VIL	Low-Level Input		1.65 to 1.95	_	-	0.15 V _{CC}	_	0.15 V _{CC}	V
	Voltage		2.3 to 5.5	-	-	0.20 V _{CC}	-	0.20 V _{CC}	
V _{OH}	High-Level Output Voltage (NLV)	V_{IN} = V_{IH} or V_{IL} I_{OH} = -100 μ A	1.65 to 5.5	V _{CC} – 0.1	V _{CC}	_	V _{CC} – 0.1	_	V
			1.65 2.3 2.7 3.0 3.0 4.5	1.29 1.9 2.2 2.4 2.3 3.8	1.52 2.1 2.3 2.6 2.5 4.2	- - - - -	1.29 1.9 2.2 2.4 2.3 3.8	- - - - -	
	High-Level Output Voltage		1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.4 2.7 2.5 4.0	- - - - - -	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	- - - - -	V
V _{OL}	Low-Level Output Voltage (NLV)	V _{IN} = V _{IH} I _{OL} = 100 μA	1.65 to 5.5	-	-	0.1	-	0.1	V
			1.65 2.3 2.7 3.0 3.0 4.5		0.08 0.2 0.2 0.24 0.26 0.31	0.24 0.3 0.4 0.4 0.55 0.55		0.24 0.3 0.4 0.4 0.55 0.55	
	Low-Level Output Voltage		1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		- 0.08 0.2 0.22 0.28 0.38 0.38	0.1 0.24 0.3 0.4 0.4 0.55 0.55	- - - - -	0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	1.65 to 5.5	-	-	±0.1	-	±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V	0	-	-	1.0	-	10	μA
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5	-	_	1.0	-	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

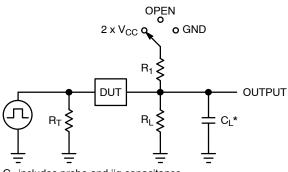
AC ELECTRICAL CHARACTERISTICS

				T _A = 25°C		– 55°C ≤ 1			
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Units
t _{PLH}	Propagation Delay	R_L = 1 M Ω , C_L = 15 pF	1.65 to 1.95	-	5.5	9.8	-	11.0	ns
τρηΓ	t _{PHL} Input A to Y (Figure 3 and 4)	$R_L = 1 M\Omega$, $C_L = 15 pF$	2.3 to 2.7	-	3.3	5.7	-	6.3	
		$R_L = 1 M\Omega$, $C_L = 15 pF$	3.0 to 3.6	-	2.7	4.1	-	4.5	
		R_L = 500 Ω , C_L = 50 pF		-	4.0	6.4	_	7.0	
		$R_L = 1 M\Omega$, $C_L = 15 pF$	4.5 to 5.5	-	2.2	3.3	-	3.6	
		R_L = 500 Ω , C_L = 50 pF		-	3.4	5.6	-	6.2	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	4.0	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

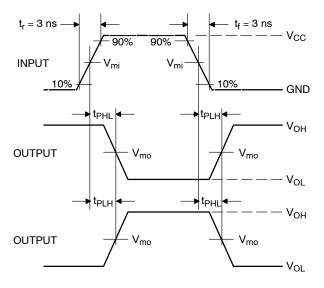


Test	Switch Position	C _L , pF	R_{L}, Ω	R ₁ , Ω		
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table				
t _{PLZ} / t _{PZL}	$2 \times V_{CC}$	50	500	500		
t _{PHZ} / t _{PZH}	GND	50	500	500		
V Dealth Carre						

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit



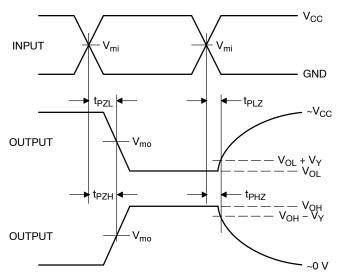


Figure 4. Switching Waveforms

		Vm		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

DEVICE ORDERING INFORMATION

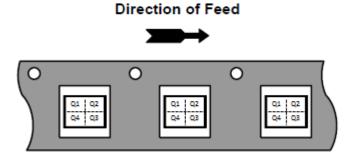
Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL27WZU04DFT2G	SC-88	M6	Q4	3000 / Tape & Reel
NL27WZU04DFT2G-L22348**	SC-88	M6	Q4	3000 / Tape & Reel
NLV27WZU04DFT2G*	SC-88	M6	Q4	3000 / Tape & Reel
NL27WZU04DBVT1G	SC-74	M6	Q4	3000 / Tape & Reel
NL27WZU04DTT1G**	TSOP-6	M6	Q4	3000 / Tape & Reel
NL27WZU04MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
NL27WZU04MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

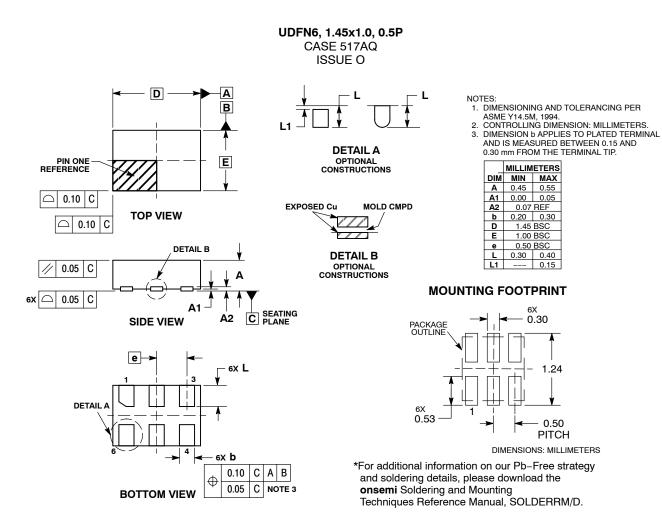
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

**Please refer to NLV specifications for this device.

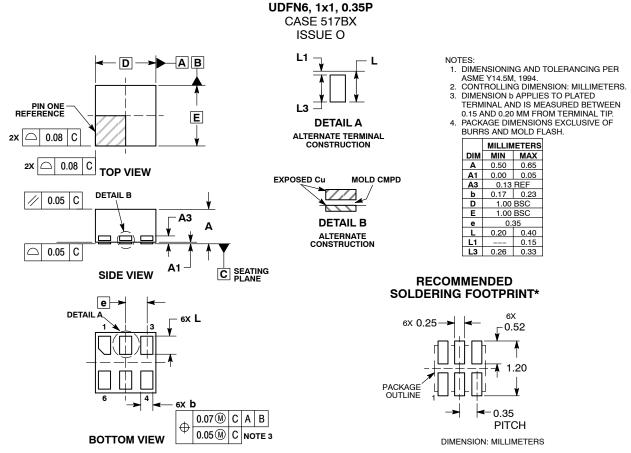
Pin 1 Orientation in Tape and Reel



PACKAGE DIMENSIONS



PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

0.15

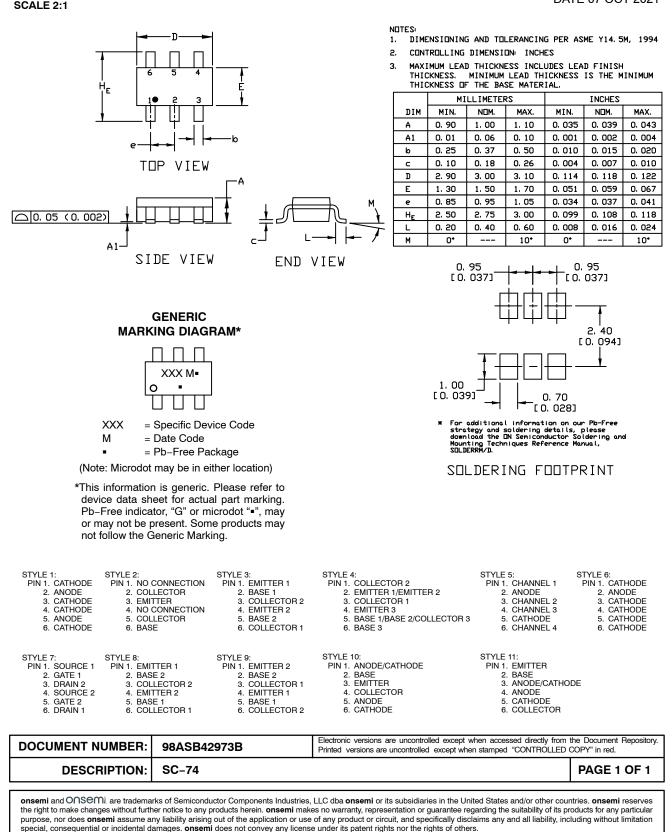
6X

1.20

onsemi

SC-74 CASE 318F ISSUE P

DATE 07 OCT 2021



onsemi

TSOP-6 CASE 318G-02 ISSUE V DATE 12 JUN 2012 SCALE 2:1 NOTES: D 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM 2 Η З. LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D 4 ¥ 12 4 GAUGE E1 Е AND E1 ARE DETERMINED AT DATUM H. 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE. ۲Ì 4 MILLIMETERS М NOTE 5 b DIM MIN NOM MAX 0.90 1.10 DETAIL Z Α 1.00 A1 0.01 0.06 0.10 b 0.25 0.38 0.50 с 0.10 0 18 0.26 D 2.90 3.00 3.10 С Е 2.50 2.75 Α 3.00 $|\cap$ 0.05 E1 1.30 1.50 1.70 e L 0.85 0.95 1.05 0.40 0.20 0.60 Δ1 L2 M 0.25 BSC DETAIL Z 0 10° STYLE 3: PIN 1. ENABLE 2. N/C STYLE 2: PIN 1. EMITTER 2 2. BASE 1 STYLE 4: PIN 1. N/C 2. V in STYLE 5: PIN 1. EMITTER 2 2. BASE 2 STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR STYLE 1: PIN 1. DRAIN 2. DRAIN 3. COLLECTOR 1 4. EMITTER 1 3. R BOOST 4. Vz 3. COLLECTOR 1 4. EMITTER 1 3. GATE 4. SOURCE 3. NOT USED 4. GROUND 3. BASE 4. EMITTER 5. ENABLE 6. LOAD 5. COLLECTOR 6. COLLECTOR 5. DRAIN 5. BASE 2 5. V in 5. BASE 1 6. V out 6. COLLECTOR 2 6. COLLECTOR 2 6. DRAIN STYLE 11: STYLE 7 STYLE 8: STYLE 9: STYLE 10: STYLE 12: PIN 1. COLLECTOR PIN 1. Vbus PIN 1. LOW VOLTAGE GATE PIN 1. D(OUT)+ PIN 1. SOURCE 1 PIN 1. I/O 2. GROUND 2. DRAIN 2 2. COLLECTOR 2. D(in) 2. DRAIN 2. GND 3. BASE 4. N/C 3. D(in)+ 4. D(out)+ 3. SOURCE 4. DRAIN 3. D(OUT)-4. D(IN)-DRAIN 2 3. I/O З. 4 I/O 4 SOURCE 2 5. COLLECT 6. EMITTER COLLECTOR 5. D(out) 6. GND 5. DRAIN 6. HIGH VOLTAGE GATE 5. VBUS 6. D(IN)+ 5. GATE 1 6. DRAIN 1/GATE 2 5. VCC 6. I/O STYLE 13: PIN 1. GATE 1 STYLE 14: PIN 1. ANODE STYLE 15: PIN 1. ANODE STYLE 16: PIN 1. ANODE/CATHODE STYLE 17: PIN 1. EMITTER 2. SOURCE 2 2. SOURCE 2. SOURCE 3. GATE 2. BASE 2. BASE 3 EMITTER 3 ANODE/CATHODE 3. GATE 2 3 GATE 4. CATHODE/DRAIN 5. CATHODE/DRAIN 4. DRAIN 2 4. DRAIN 4 COLLECTOR ANODE CATHODE 5. SOURCE 1 5. N/C 5. ANODE 5. 6. DRAIN 1 6. CATHODE/DRAIN 6. CATHODE CATHODE COLLECTOR 6. 6. GENERIC RECOMMENDED **MARKING DIAGRAM*** SOLDERING FOOTPRINT* 0.60 XXXAYW= XXX M= 0 o 1LI 6X 3.20 IC STANDARD 0.95 XXX = Specific Device Code XXX = Specific Device Code А =Assembly Location Μ = Date Code Y = Year = Pb-Free Package W = Work Week 0.95 = Pb-Free Package PITCH DIMENSIONS: MILLIMETERS *This information is generic. Please refer to device data *For additional information on our Pb-Free strategy and soldering sheet for actual part marking. Pb-Free indicator, "G" details, please download the ON Semiconductor Soldering and or microdot "•", may or may not be present. Some Mounting Techniques Reference Manual, SOLDERRM/D. products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. DOCUMENT NUMBER 00468440000

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0.043

0.004





- XXX = Specific Device Code

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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